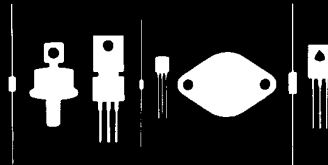


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145 Adams Avenue
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2N4354 MPS4354
2N4355 MPS4355
2N4356 MPS4356

JEDEC TO-105 JEDEC TO-92(EBC)

SILICON PNP TRANSISTORS

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4354, MPS4354 series types are Silicon PNP Small Signal Transistors designed for general purpose amplifier and switching applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	2N4354 MPS4354	2N4355 MPS4355	2N4356 MPS4356	UNIT
Collector-Base Voltage	V _{CB0}	60	60	80	V
Collector-Emitter Voltage	V _{CEO}	60	60	80	V
Emitter-Base Voltage	V _{EB0}	5.0	5.0	5.0	V
Collector Current	I _C	1.0	1.0	1.0	A
Power Dissipation, MPS Types (TO-92 CASE)	P _D		625		mW
Power Dissipation, 2N Types (TO-105 CASE)	P _D		350		mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 TO +150			°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N4354 MPS4354		2N4355 MPS4355		2N4356 MPS4356		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{CB0}	V _{CB} =50V		50		50		50	nA
I _{CB0}	V _{CB} =50V, T _A =75°C		5.0		5.0		5.0	μA
I _{EB0}	V _{EB} =4.0V		100		100		100	nA
BV _{CB0}	I _C =10μA	60		60		80		V
BV _{EB0}	I _E =10μA	5.0		5.0		5.0		V
BV _{CEO}	I _C =10mA	60		60		80		V
V _{CE} (SAT)	I _C =150mA, I _B =15mA		0.15		0.15		0.15	V
V _{CE} (SAT)	I _C =500mA, I _B =50mA		0.5		0.5		0.5	V
V _{CE} (SAT)	I _C =1.0A, I _B =100mA		-		1.0		-	V
V _{BE} (SAT)	I _C =150mA, I _B =15mA		0.9		0.9		0.9	V
V _{BE} (SAT)	I _C =500mA, I _B =50mA		1.1		1.1		1.1	V
V _{BE} (SAT)	I _C =1.0A, I _B =100mA		-		1.2		-	V
V _{BE} (ON)	V _{CE} =0.5V, I _C =500mA		1.1		1.1		1.1	V
V _{BE} (ON)	V _{CE} =1.0V, I _C =1.0A		-		1.2		-	V
h _{FE}	V _{CE} =10V, I _C =100μA	25		60		25		
h _{FE}	V _{CE} =10V, I _C =1.0mA	40		75		40		
h _{FE}	V _{CE} =10V, I _C =10mA	50	500	100	400	50	250	
h _{FE}	V _{CE} =10V, I _C =100mA	40		75		40		
h _{FE}	V _{CE} =10V, I _C =500mA	30		75		30		
f _T	V _{CE} =10V, I _C =50mA, f=100MHz	100	500	100	500	100	500	MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		30		30		30	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=1.0MHz		110		110		100	pF
t _{on}	V _{CC} =30V, I _C =500mA, I _{B1} =50mA		100		100		100	ns
t _{off}	V _{CC} =30V, I _C =500mA, I _{B1} =I _{B2} =50mA		400		400		400	ns
NF	V _{CE} =10V, I _C =100μA, R _S =1.0kΩ, f=1.0kHz, BW=1.0Hz		3.0		3.0		3.0	dB